

AMENDMENTS IN THE CLAIMS:

1. (Original) A method of growing a p-type nitride semiconductor material by molecular beam epitaxy, the method comprising supplying bis(cyclopentadienyl)magnesium (Cp_2Mg) during the growth process.
2. (Currently Amended) A method as claimed in claim 1_a wherein the nitride semiconductor material is p-type (Ga,Al)N.
3. (Currently Amended) A method as claimed in claim 1_a and comprising supplying ammonia gas during the growth process.
4. (Currently Amended) A method as claimed in claim 1_a and comprising supplying ammonia gas, gallium and Cp_2Mg to a growth chamber, thereby to grow a layer of p-type GaN.
5. (Currently Amended) A method as claimed in claim 1_a and comprising supplying ammonia gas, aluminium, gallium and Cp_2Mg to a growth chamber, thereby to grow a layer of p-type AlGaN.
6. (Currently Amended) A method as claimed in 1_a and comprising changing the supply rate of Cp_2Mg during the growth of the nitride semiconductor material.
7. (Cancelled)
8. (Currently Amended) A method as claimed in claim 1_a wherein the growth process is carried out at a temperature of at least 800 °C.
9. (Currently Amended) A method as claimed in claim 1_a wherein the growth process is carried out at a temperature of at least 850 °C.

10. (Currently Amended) A method as claimed in claim 1, wherein the growth process is carried out at a temperature of at least 920 °C.
11. (Currently Amended) A method as claimed in claim 1, wherein the growth process is carried out at a temperature of at least 950 °C.
12. (Currently Amended) A method as claimed in claim 1, wherein the growth process is carried out at a temperature of 960 °C or below.
13. (Currently Amended) A method as claimed in claim 1, and comprising supplying Cp_2Mg at a beam equivalent pressure of at least 1×10^{-9} mbar.
14. (Currently Amended) A method as claimed in claim 1, and comprising supplying Cp_2Mg at a beam equivalent pressure of at least 3×10^{-9} mbar.
15. (Currently Amended) A method as claimed in claim 1, and comprising supplying Cp_2Mg at a beam equivalent pressure of 1×10^{-7} mbar or below.
16. (Currently Amended) A method as claimed in claim 1, and comprising supplying Cp_2Mg at a beam equivalent pressure of 1.5×10^{-8} mbar or below.
17. (Currently Amended) A method as claimed in claim 4, and comprising supplying elemental gallium at a beam equivalent pressure of at least 1×10^{-8} mbar.
18. (Currently Amended) A method as claimed in claim 4, and comprising supplying elemental gallium at a beam equivalent pressure of 1×10^{-5} mbar or below.

19. (Currently Amended) A method as claimed in claim 5, ~~and~~ comprising supplying elemental gallium and elemental aluminium at an overall beam equivalent pressure of at least 1×10^{-8} mbar.
20. (Currently Amended) A method as claimed in claim 5, ~~and~~ comprising supplying elemental gallium and elemental aluminium at an overall beam equivalent pressure of 1×10^{-5} mbar or below.
21. (Previously Presented) A p-type nitride semiconductor material grown by a method defined in claim 1.
22. (Previously Presented) A semiconductor device comprising a layer of a p-type nitride semiconductor material grown by a method defined in claim 1.
23. (Currently Amended) A semiconductor device as claimed in claim 22, wherein the layer of nitride semiconductor material is a layer of p-type (Ga,Al)N.